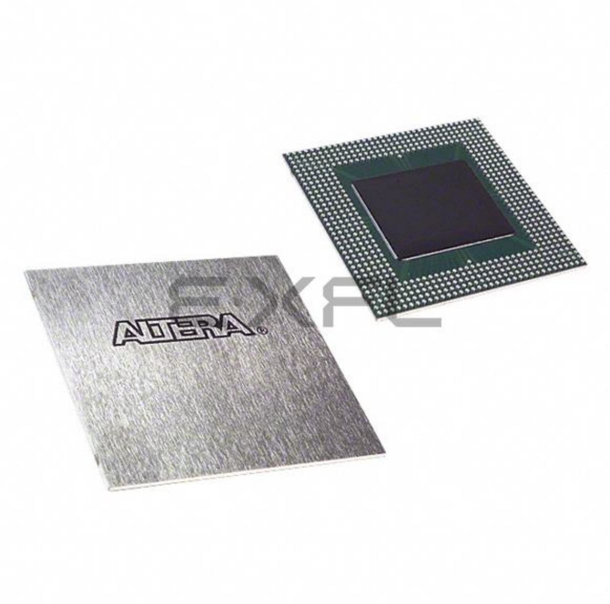
Intel - EP20K1000CB652C7N Datasheet



Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	3840
Number of Logic Elements/Cells	38400
Total RAM Bits	327680
Number of I/O	488
Number of Gates	1772000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	652-BGA
Supplier Device Package	652-BGA (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k1000cb652c7n

...and More Features

- Low-power operation design
  - 1.8-V supply voltage (see Table 2)
  - Copper interconnect reduces power consumption
  - MultiVolt™ I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - ESBs offering programmable power-saving mode
- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
  - Built-in low-skew clock tree
  - Up to eight global clock signals
  - ClockLock™ feature reducing clock delay and skew
  - ClockBoost™ feature providing clock multiplication and division
  - ClockShift™ feature providing programmable clock phase and delay shifting
- Powerful I/O features
  - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) ***PCI Local Bus Specification, Revision 2.2*** for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
  - Support for high-speed external memories, including DDR synchronous dynamic RAM (SDRAM) and ZBT static RAM (SRAM)
  - 16 input and 16 output LVDS channels at 840 megabits per second (Mbps)
  - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
  - MultiVolt I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - Programmable clamp to V_{CCIO}
  - Individual tri-state output enable control for each pin
  - Programmable output slew-rate control to reduce switching noise
  - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, SSTL-3 and SSTL-2, GTL+, and HSTL Class I
  - Supports hot-socketing operation
  - Pull-up on I/O pins before and during configuration

Table 2. APEX 20KC Supply Voltages

Feature	Voltage
Internal supply voltage (V_{CCINT})	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	1.8 V, 2.5 V, 3.3 V, 5.0 V *(1)*

Note to Table 2:

(1) APEX 20KC devices can be 5.0-V tolerant by using an external resistor.

Cascade Chain

With the cascade chain, the APEX 20KC architecture can implement functions with a very wide fan-in. Adjacent LUTs can compute portions of a function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical AND or logical OR (via De Morgan's inversion) to connect the outputs of adjacent LEs. Each additional LE provides four more inputs to the effective width of a function, with a short cascade delay. Cascade chain logic can be created automatically by the Quartus II Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than ten LEs are implemented automatically by linking LABs together. For enhanced fitting, a long cascade chain skips alternate LABs in a MegaLAB structure. A cascade chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure. Figure 7 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in.

Figure 7. APEX 20KC Cascade Chain

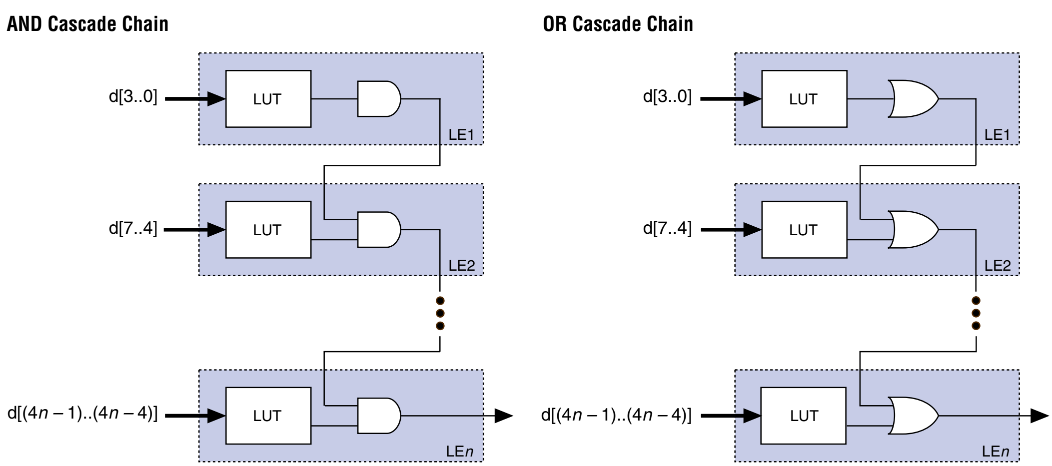
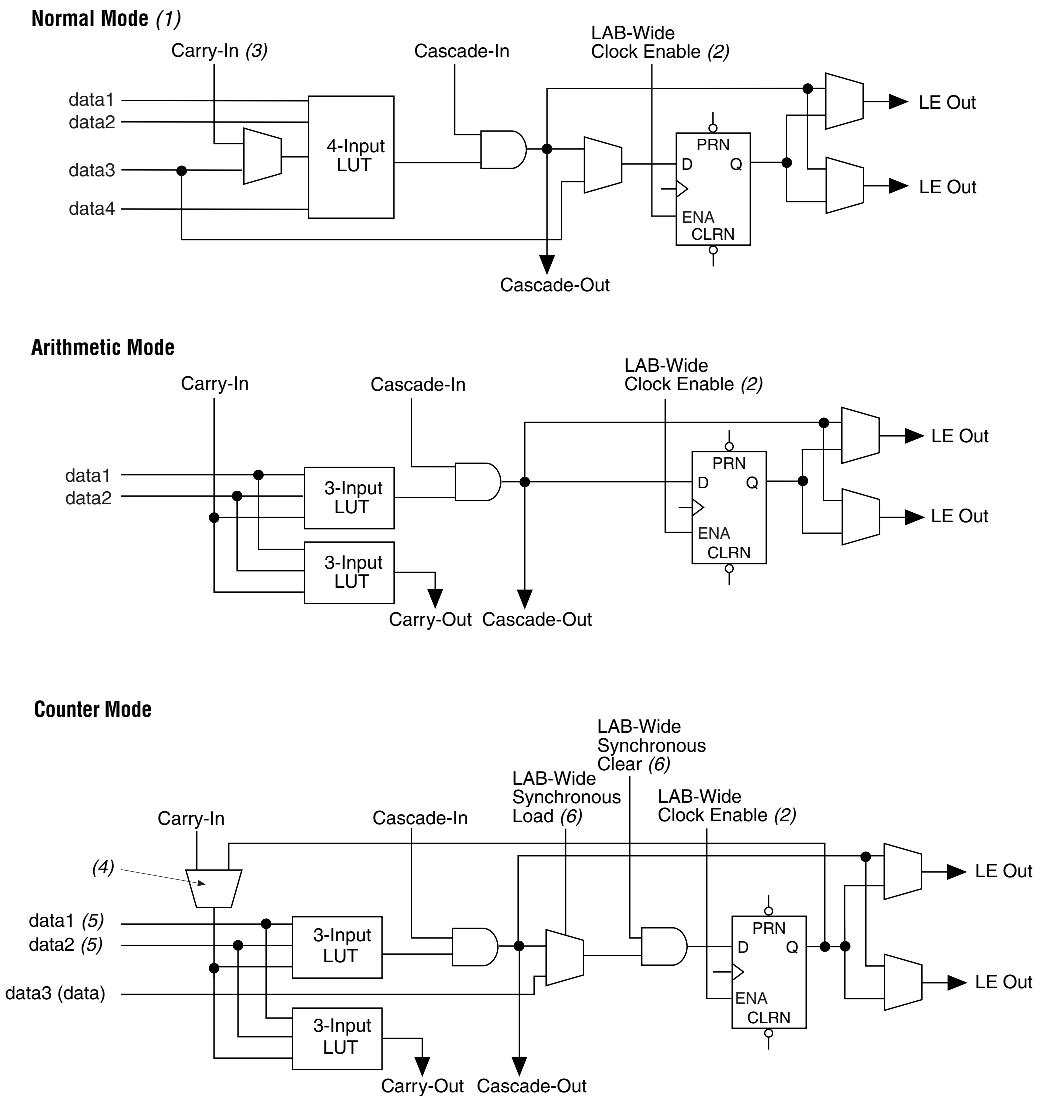


Figure 8. APEX 20KC LE Operating Modes

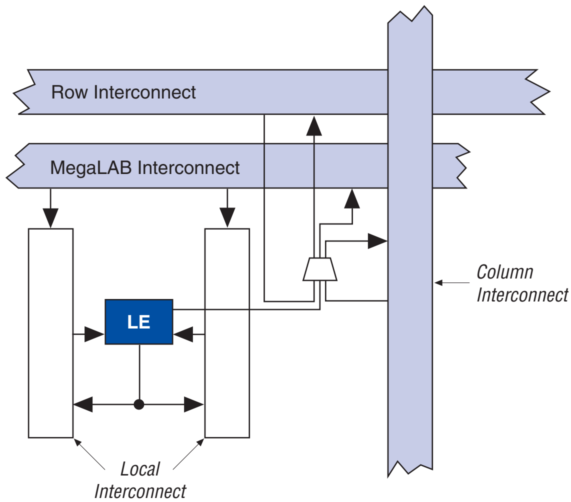


Notes to Figure 8:

(1) LEs in normal mode support register packing.
(2) There are two LAB-wide clock enables per LAB.
(3) When using the carry-in in normal mode, the packed register feature is unavailable.
(4) A register feedback multiplexer is available on LE1 of each LAB.
(5) The `DATA1` and `DATA2` input signals can supply counter enable, up or down control, or register feedback signals for LEs other than the second LE in an LAB.
(6) The LAB-wide synchronous clear and LAB wide synchronous load affect all registers in an LAB.

Figure 11 shows the intersection of a row and column interconnect, and how these forms of interconnects and LEs drive each other.

Figure 11. Driving the FastTrack Interconnect



APEX 20KC devices include an enhanced interconnect structure for faster routing of input signals with high fan-out. Column I/O pins can drive the FastRow™ interconnect, which routes signals directly into the local interconnect without having to drive through the MegaLAB interconnect. The FastRow lines traverse two MegaLAB structures. Also, these pins can drive the local interconnect directly for fast setup times. On EP20K400C and larger devices, the FastRow interconnect drives the two MegaLAB structures in the top left corner, the two MegaLAB structures in the two right corner, the two MegaLAB structures in the bottom left corner, and the two MegaLAB structures in the bottom right corner. On EP20K200C and smaller devices, FastRow interconnect drives the two MegaLAB structures on the top and the two MegaLAB structures on the bottom of the device. On all devices, the FastRow interconnect drives all local interconnect in the appropriate MegaLAB structures except the end local interconnect on the side of the MegaLAB opposite the ESB. Pins using the FastRow interconnect achieve a faster set-up time, as the signal does not need to use a MegaLAB interconnect line to reach the destination LE. Figure 12 shows the FastRow interconnect.

Figure 12. APEX 20KC FastRow Interconnect

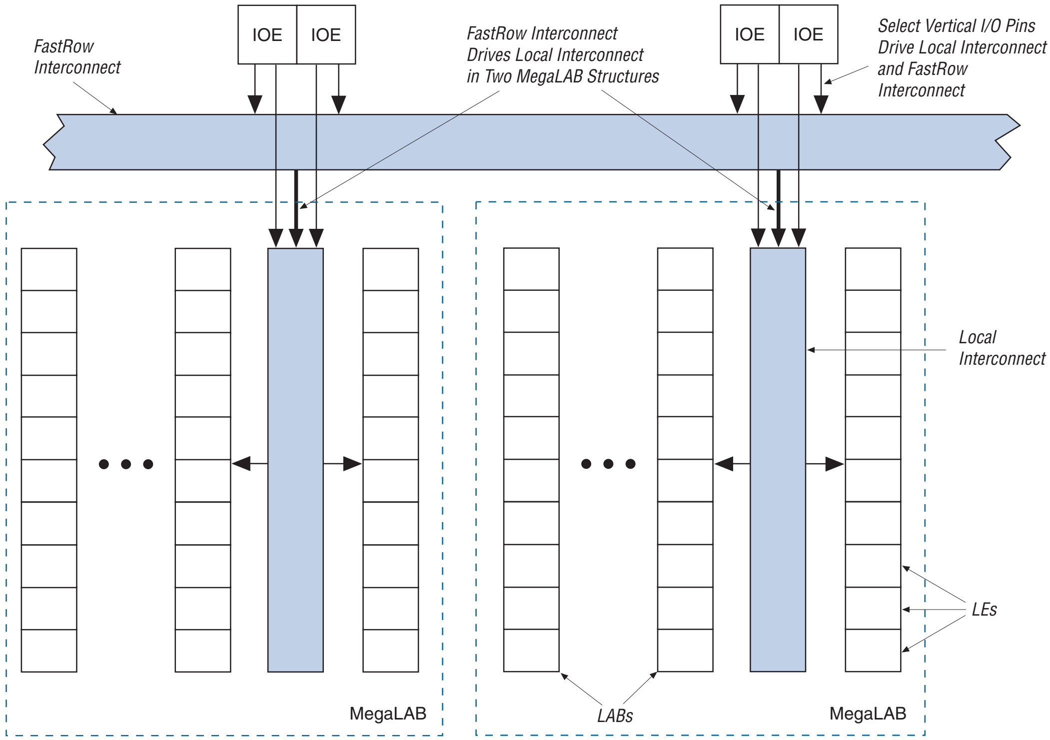
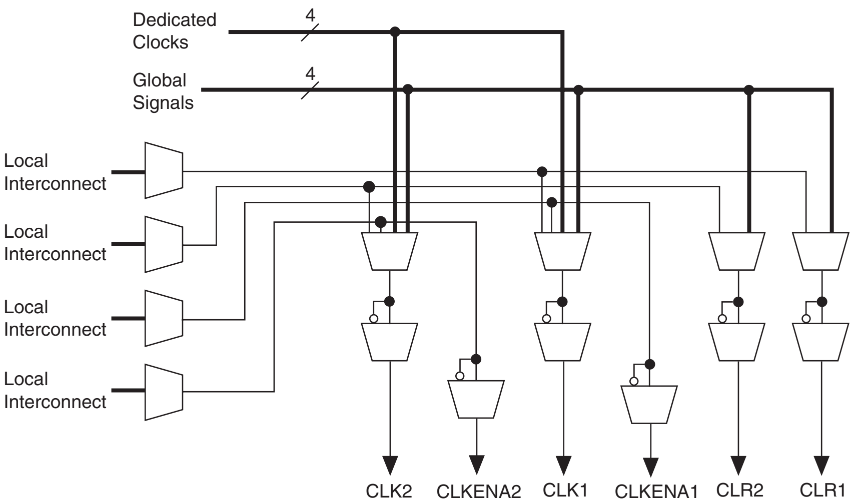


Table 8 summarizes how various elements of the APEX 20KC architecture drive each other.

The programmable register also supports an asynchronous clear function. Within the ESB, two asynchronous clears are generated from global signals and the local interconnect. Each macrocell can either choose between the two asynchronous clear signals or choose to not be cleared. Either of the two clear signals can be inverted within the ESB. Figure 15 shows the ESB control logic when implementing product-terms.

Figure 15. ESB Product-Term Mode Control Logic



Parallel Expanders

Parallel expanders are unused product terms that can be allocated to a neighboring macrocell to implement fast, complex logic functions. Parallel expanders allow up to 32 product terms to feed the macrocell OR logic directly, with two product terms provided by the macrocell and 30 parallel expanders provided by the neighboring macrocells in the ESB.

The Quartus II Compiler can allocate up to 15 sets of up to two parallel expanders per set to the macrocells automatically. Each set of two parallel expanders incurs a small, incremental timing delay. Figure 16 shows the APEX 20KC parallel expanders.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

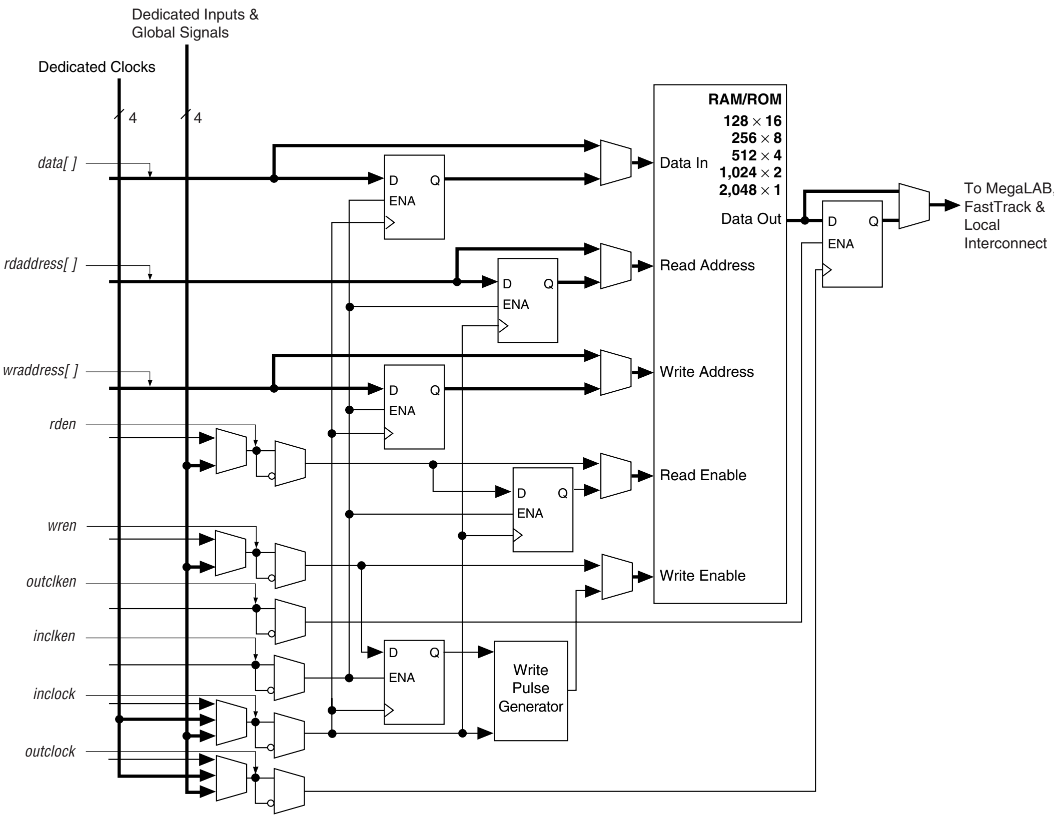
When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Input/Output Clock Mode

The input/output clock mode contains two clocks. One clock controls all registers for inputs into the ESB: data input, WE, RE, read address, and write address. The other clock controls the ESB data output registers. The ESB also supports clock enable and asynchronous clear signals; these signals also control the reading and writing of registers independently. Input/output clock mode is commonly used for applications where the reads and writes occur at the same system frequency, but require different clock enable signals for the input and output registers. Figure 21 shows the ESB in input/output clock mode.

Figure 21. ESB in Input/Output Clock Mode *Note (1)*



Note to Figure 21:

(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.

CAM is used for high-speed search operations. When searching for data within a RAM block, the search is performed serially. Thus, finding a particular data word can take many cycles. CAM searches all addresses in parallel and outputs the address storing a particular word. When a match is found, a match flag is set high. Figure 23 shows the CAM block diagram.

APEX 20KC devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KC IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KC IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II Compiler sets these delays by default to minimize setup time while providing a zero hold time.

The Quartus II Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20KC IOE offers one output enable per pin, the Quartus II Compiler can emulate open-drain operation efficiently.

The APEX 20KC IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

Table 9 describes the APEX 20KC programmable delays and their logic options in the Quartus II software.

Table 9. APEX 20KC Programmable Delay Chains

Programmable Delay	Quartus II Logic Option
Input pin to core delay	Decrease input delay to internal cells
Input pin to input register delay	Decrease input delay to input registers
Core to output register delay	Decrease input delay to output register
Output register t_{CO} delay	Increase delay to output pin
Clock enable delay	Increase clock enable delay

The Quartus II Compiler can program these delays automatically to minimize setup time while providing a zero hold time.

Notes to Figure 25:
(1) This programmable delay has four settings: off and three levels of delay.
(2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 26 shows how a row IOE connects to the interconnect.

Figure 26. Row IOE Connection to the Interconnect

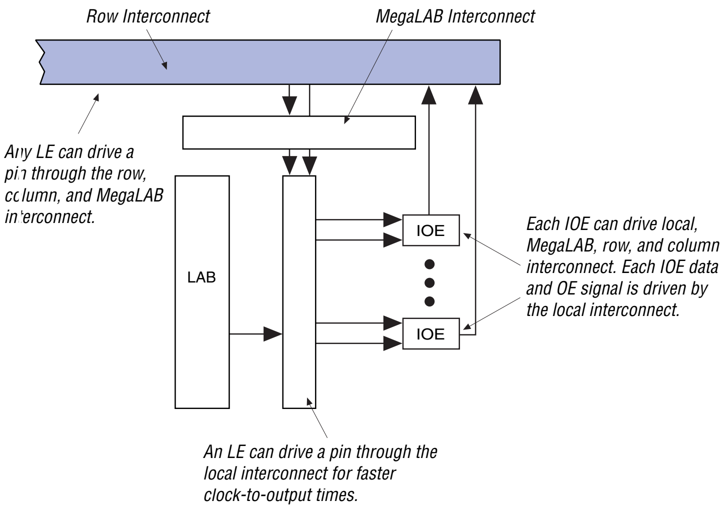


Table 18. APEX 20KC Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_I	Input voltage	*(2)*, *(5)*	–0.5	4.1	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time (10% to 90%)			40	ns
t_F	Input fall time (90% to 10%)			40	ns

Table 19. APEX 20KC Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	Input pin leakage current *(8)*	V_I = 3.6 to 0.0 V	–10		10	μA
I_{OZ}	Tri-stated I/O pin leakage current *(8)*	V_O = 4.1 to –0.5 V	–10		10	μA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -7 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -8, -9 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(9)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(9)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(9)*	60		150	kΩ

DC operating specifications on APEX 20KC I/O standards are listed in Tables 21 to 35.

Table 28. GTL+ I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{TT}	Termination voltage		1.35	1.5	1.65	V
V_{REF}	Reference voltage		0.88	1.0	1.12	V
V_{IH}	High-level input voltage		V_{REF} + 0.1			V
V_{IL}	Low-level input voltage				V_{REF} – 0.1	V
V_{OL}	Low-level output voltage	I_{OL} = 36 mA *(2)*			0.65	V

Table 29. SSTL-2 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V
V_{OH}	High-level output voltage	I_{OH} = –7.6 mA *(1)*	V_{TT} + 0.57			V
V_{OL}	Low-level output voltage	I_{OL} = 7.6 mA *(2)*			V_{TT} – 0.57	V

Figure 33. ESB Asynchronous Timing Waveforms

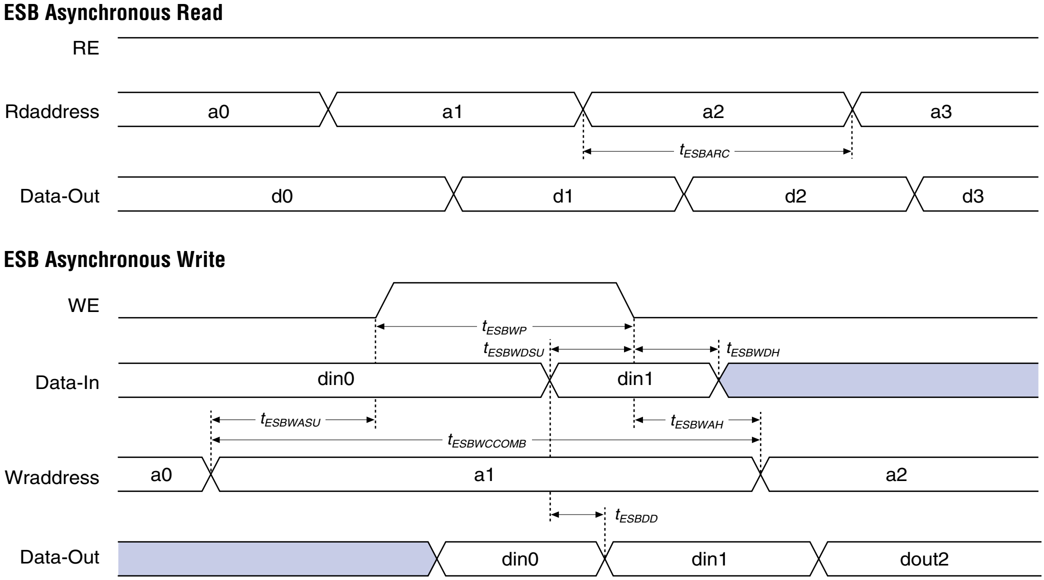


Figure 34. ESB Synchronous Timing Waveforms

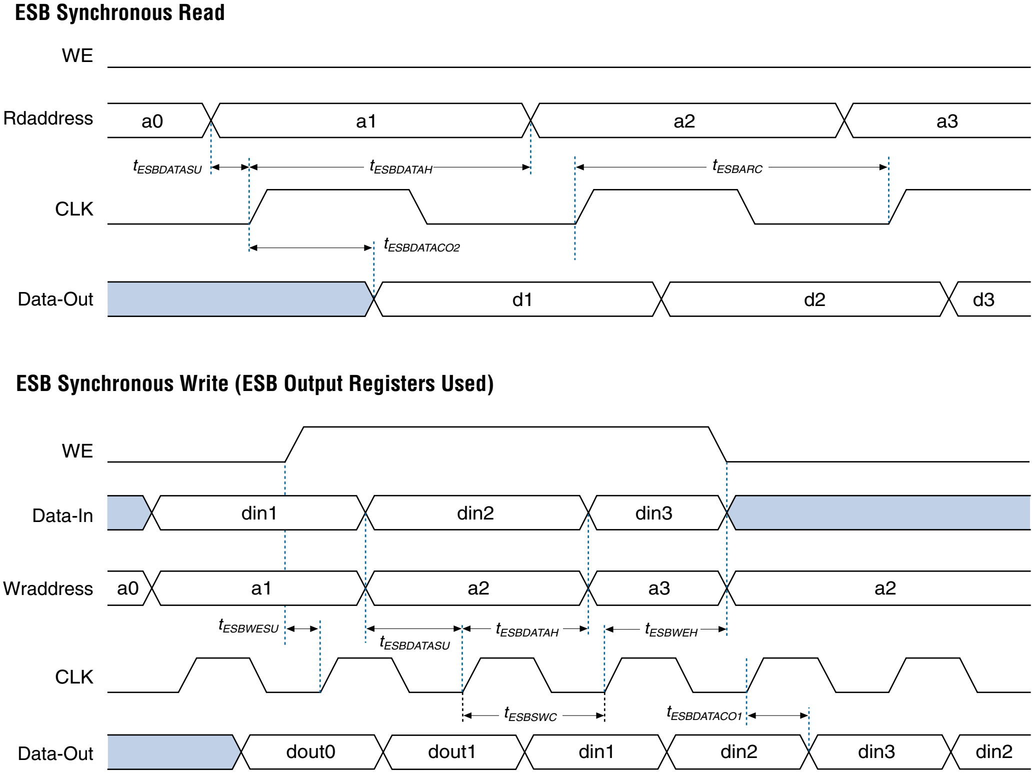


Figure 35 shows the timing model for bidirectional I/O pin timing.

Table 37. APEX 20KC f_{MAX} ESB Timing Parameters	
Symbol	**Parameter**
t_{ESBARC}	ESB asynchronous read cycle time
t_{ESBSRC}	ESB synchronous read cycle time
t_{ESBAWC}	ESB asynchronous write cycle time
t_{ESBSWC}	ESB synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB macrocell input to non-registered output
$t_{PTERMSU}$	ESB macrocell register setup time before clock
$t_{PTERMCO}$	ESB macrocell register clock-to-output delay

Table 38. APEX 20KC f_{MAX} Routing Delays	
Symbol	**Parameter**
t_{F1-4}	Fan-out delay estimate using local interconnect
t_{F5-20}	Fan-out delay estimate using MegaLab interconnect
t_{F20+}	Fan-out delay estimate using FastTrack interconnect

Table 51. EP20K400C f_{MAX} ESB Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.30		1.51		1.69	ns
t_{ESBSRC}		2.35		2.49		2.72	ns
t_{ESBAWC}		2.92		3.46		3.86	ns
t_{ESBSWC}		3.05		3.44		3.85	ns
$t_{ESBWASU}$	0.45		0.50		0.54		ns
t_{ESBWAH}	0.44		0.50		0.55		ns
$t_{ESBWDSU}$	0.57		0.63		0.68		ns
t_{ESBWDH}	0.44		0.50		0.55		ns
$t_{ESBRASU}$	1.25		1.43		1.56		ns
t_{ESBRAH}	0.00		0.03		0.11		ns
$t_{ESBWESU}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	2.01		2.27		2.45		ns
$t_{ESBWADDRSU}$	–0.20		–0.24		–0.28		ns
$t_{ESBRADDRSU}$	0.02		0.00		–0.02		ns
$t_{ESBDATACO1}$		1.09		1.28		1.43	ns
$t_{ESBDATACO2}$		2.10		2.52		2.82	ns
t_{ESBDD}		2.50		2.97		3.32	ns
t_{PD}		1.48		1.78		2.00	ns
$t_{PTERMSU}$	0.58		0.72		0.81		ns
$t_{PTERMCO}$		1.10		1.29		1.45	ns

Table 52. EP20K400C f_{MAX} Routing Delays

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.15		0.17		0.19	ns
t_{F5-20}		0.94		1.06		1.25	ns
t_{F20+}		1.73		1.96		2.30	ns

Table 53. EP20K400C Minimum Pulse Width Timing Parameters							
Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 54. EP20K400C External Timing Parameters							
Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.37		1.52		1.64		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.25	2.00	4.61	2.00	5.03	ns
$t_{INSUPLL}$	0.80		0.91		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.27	0.50	2.55	-	-	ns

Table 67. EP20K1000C External Bidirectional Timing Parameters							
Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	1.86		2.54		3.15		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	4.63	2.00	5.26	2.00	5.69	ns
$t_{XZBIDIR}$		8.98		9.89		10.67	ns
$t_{ZXBIDIR}$		8.98		9.89		10.67	ns
$t_{INSUBIDIRPLL}$	4.17		5.27		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.32	0.50	2.55	-	-	ns
$t_{XZBIDIRPLL}$		6.67		7.18		-	ns
$t_{ZXBIDIRPLL}$		6.67		7.18		-	ns

Tables 68 and 69 show selectable I/O standard input and output delays for APEX 20KC devices. If you select an I/O standard input or output delay other than LVCMOS, add the delay for the selected speed grade to the LVCMOS value.

Table 68. Selectable I/O Standard Input Delays							
Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.00		0.00	ns
1.8 V		0.04		0.11		0.14	ns
PCI		0.00		0.04		0.03	ns
GTL+		–0.30		0.25		0.23	ns
SSTL-3 Class I		–0.19		–0.13		–0.13	ns
SSTL-3 Class II		–0.19		–0.13		–0.13	ns
SSTL-2 Class I		–0.19		–0.13		–0.13	ns
SSTL-2 Class II		–0.19		–0.13		–0.13	ns
LVDS		–0.19		–0.17		–0.16	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

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